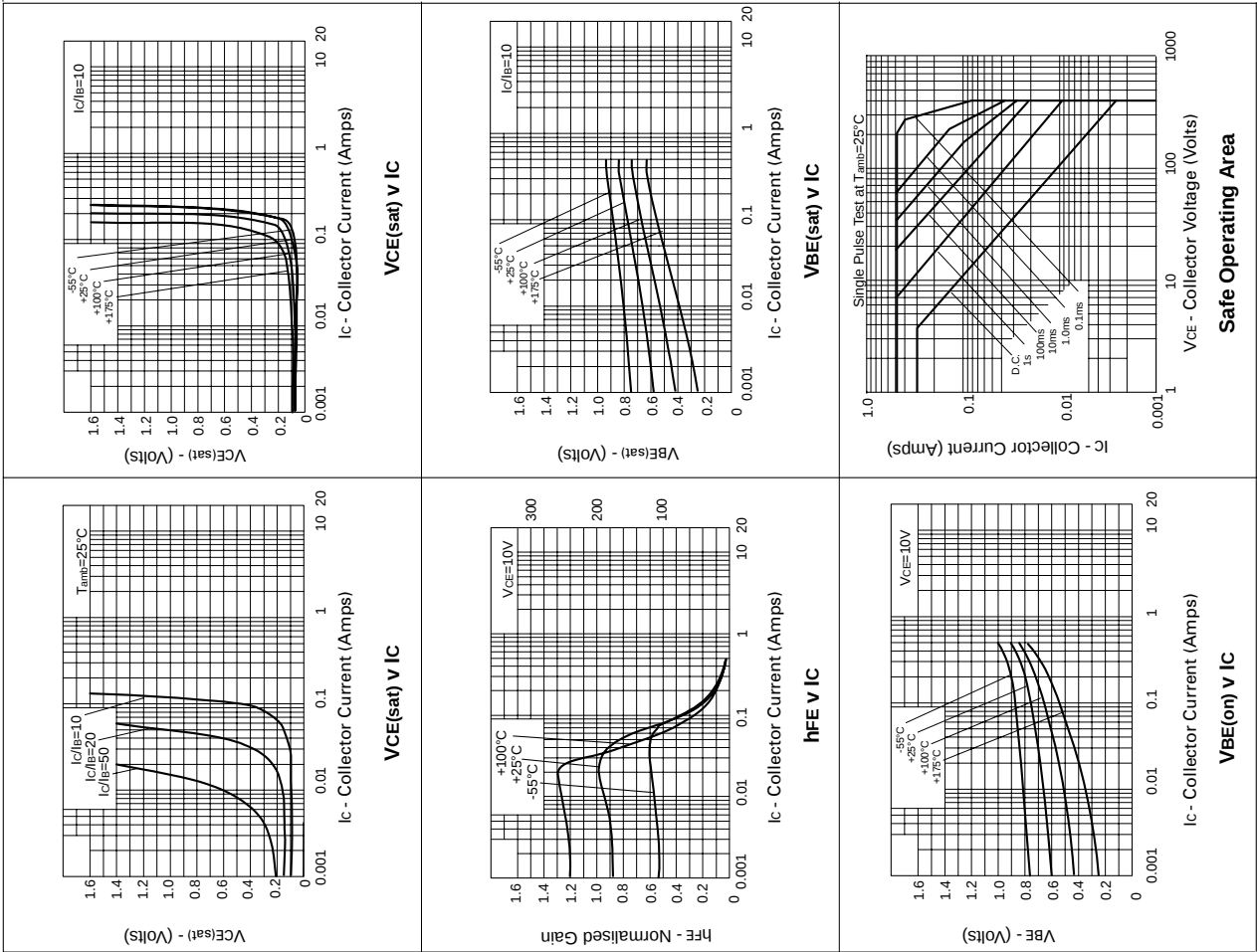


ZTX458

NPN SILICON PLANAR MEDIUM POWER
HIGH VOLTAGE TRANSISTOR
ZTX458

TYPICAL CHARACTERISTICS

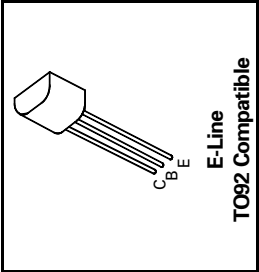


ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V _{CBO}	400	V
Collector-Emitter Voltage	V _{CEO}	400	V
Emitter-Base Voltage	V _{EBO}	5	V
Continuous Collector Current	I _C	300	mA
Power Dissipation at T _{amb} =25°C	P _{tot}	1	W
Operating and Storage Temperature Range	T _j ; T _{stg}	-55 to +200	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	V _{(BR)CBO}	400			V	I _C =100μA
Collector-Emitter Breakdown Voltage	V _{CEO(sus)}	400			V	I _C =10mA *
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5			V	I _E =100μA
Collector Cut-Off Current	I _{CBO}			100	nA	V _{CB} =320V
Collector Cut-Off Current	I _{CES}			100	nA	V _{CE} =320V
Emitter Cut-Off Current	I _{EBO}			100	nA	V _{EB} =4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.2 0.5	V	I _C =20mA, I _B =2mA I _C =50mA, I _B =6mA
Base-Emitter Saturation Voltage	V _{BE(sat)}			0.9	V	I _C =50mA, I _B =5mA
Base-Emitter Turn On Voltage	V _{BE(on)}			0.9	V	I _C =50mA, V _{CE} =10V
Static Forward Current Transfer Ratio	h _{FE}	100 100 15		300		I _C =1mA, V _{CE} =10V I _C =50mA, V _{CE} =10V I _C =100mA, V _{CE} =10V *
Transition Frequency	f _T	50			MHz	I _C =10mA, V _{CE} =20V f=20MHz
Collector-Base Breakdown Voltage	C _{obo}			5	pF	V _{CB} =20V, f=1MHz



- FEATURES**
- * 400 Volt V_{CEO}
 - * 0.5 Amp continuous current
 - * P_{tot}= 1 Watt